

High Voltage Thyristor \ Diode Module

$$V_{RRM} = 2 \times 2200 \text{ V}$$

$$I_{TAV} = 75 \text{ A}$$

$$V_T = 1.21 \text{ V}$$

Phase leg

Part number

MCNA75PD2200TB



Backside: isolated

 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

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Rectifier			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			2300	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			2200	V
I_{RD}	reverse current, drain current	$V_{R/D} = 2200 V$	$T_{VJ} = 25^{\circ}C$		100	μA
		$V_{R/D} = 2200 V$	$T_{VJ} = 140^{\circ}C$		10	mA
V_T	forward voltage drop	$I_T = 75 A$	$T_{VJ} = 25^{\circ}C$		1.24	V
		$I_T = 150 A$			1.51	V
		$I_T = 75 A$	$T_{VJ} = 125^{\circ}C$		1.21	V
		$I_T = 150 A$			1.58	V
I_{TAV}	average forward current	$T_C = 85^{\circ}C$	$T_{VJ} = 140^{\circ}C$		75	A
$I_{T(RMS)}$	RMS forward current	180° sine			118	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 140^{\circ}C$		0.84	V
r_T	slope resistance				5	m Ω
R_{thJC}	thermal resistance junction to case				0.38	K/W
R_{thCH}	thermal resistance case to heatsink			0.2		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		302	W
I_{TSM}	max. forward surge current	$t = 10 ms$; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$		1.40	kA
		$t = 8,3 ms$; (60 Hz), sine	$V_R = 0 V$		1.51	kA
		$t = 10 ms$; (50 Hz), sine	$T_{VJ} = 140^{\circ}C$		1.19	kA
		$t = 8,3 ms$; (60 Hz), sine	$V_R = 0 V$		1.29	kA
I^2t	value for fusing	$t = 10 ms$; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$		9.80	kA ² s
		$t = 8,3 ms$; (60 Hz), sine	$V_R = 0 V$		9.49	kA ² s
		$t = 10 ms$; (50 Hz), sine	$T_{VJ} = 140^{\circ}C$		7.08	kA ² s
		$t = 8,3 ms$; (60 Hz), sine	$V_R = 0 V$		6.87	kA ² s
C_J	junction capacitance	$V_R = 700 V$ $f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		39	pF
P_{GM}	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 140^{\circ}C$		10	W
		$t_p = 300 \mu s$			5	W
P_{GAV}	average gate power dissipation				0.5	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 140^{\circ}C$; $f = 50 Hz$ repetitive, $I_T = 225 A$			150	A/ μs
		$t_p = 200 \mu s$; $di_G/dt = 0.45 A/\mu s$; $I_G = 0.45 A$; $V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 75 A$			500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	$T_{VJ} = 140^{\circ}C$		1000	V/ μs
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		1.4	V
			$T_{VJ} = -40^{\circ}C$		1.6	V
I_{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		95	mA
			$T_{VJ} = -40^{\circ}C$		200	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}C$		0.2	V
I_{GD}	gate non-trigger current				10	mA
I_L	latching current	$t_p = 10 \mu s$	$T_{VJ} = 25^{\circ}C$		200	mA
		$I_G = 0.45 A$; $di_G/dt = 0.45 A/\mu s$				
I_H	holding current	$V_D = 6 V$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		200	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$ $I_G = 0.45 A$; $di_G/dt = 0.45 A/\mu s$	$T_{VJ} = 25^{\circ}C$		2	μs
t_q	turn-off time	$V_R = 100 V$; $I_T = 75 A$; $V = \frac{2}{3} V_{DRM}$ $di/dt = 10 A/\mu s$ $dv/dt = 20 V/\mu s$ $t_p = 200 \mu s$	$T_{VJ} = 125^{\circ}C$		500	μs



Package TO-240AA				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I_{RMS}	RMS current	per terminal			200	A	
T_{VJ}	virtual junction temperature		-40		140	°C	
T_{op}	operation temperature		-40		125	°C	
T_{stg}	storage temperature		-40		125	°C	
Weight					81	g	
M_D	mounting torque		2.5		4	Nm	
M_T	terminal torque		2.5		4	Nm	
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	13.0	9.7		mm	
$d_{Spb/Apb}$		terminal to backside	16.0	16.0		mm	
V_{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA		4800	V	
		t = 1 minute			4000	V	



Part description

- M = Module
- C = Thyristor (SCR)
- N = High Voltage Thyristor
- A = ($\geq 2000V$)
- 75 = Current Rating [A]
- PD = Phase leg
- 2200 = Reverse Voltage [V]
- TB = TO-240AA-1B

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCNA75PD2200TB	MCNA75PD2200TB	Box	36	520482

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 140^{\circ}C$



Thyristor

$V_{0\ max}$	threshold voltage	0.84	V
$R_{0\ max}$	slope resistance *	3.7	mΩ

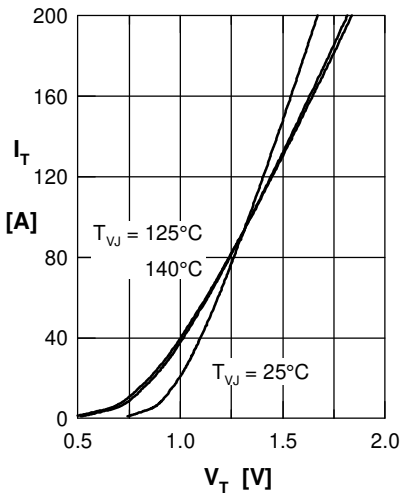
Thyristor


Fig. 1 Forward characteristics

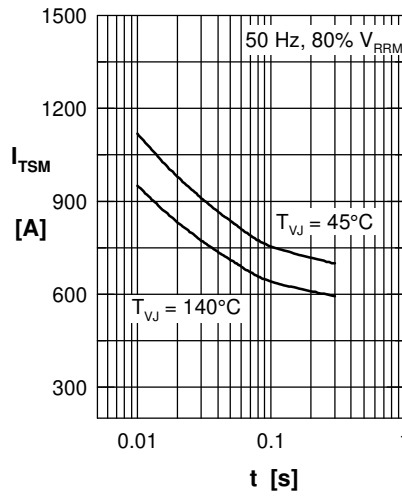
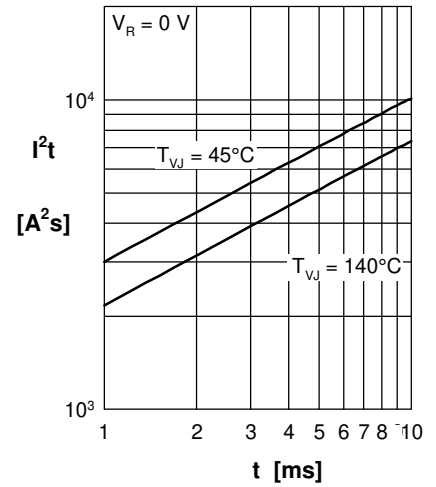
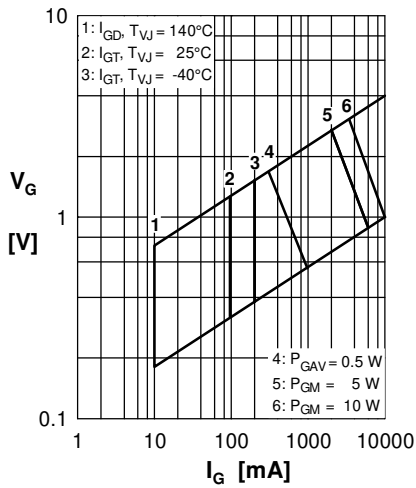

 Fig. 2 Surge overload current I_{TSM} : crest value, t: duration

 Fig. 3 I^2t versus time (1-10 s)


Fig. 4 Gate voltage & gate current

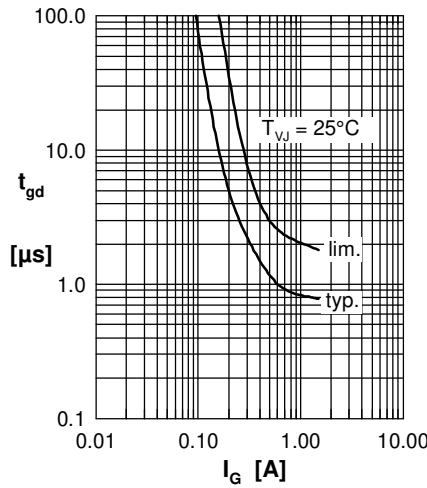
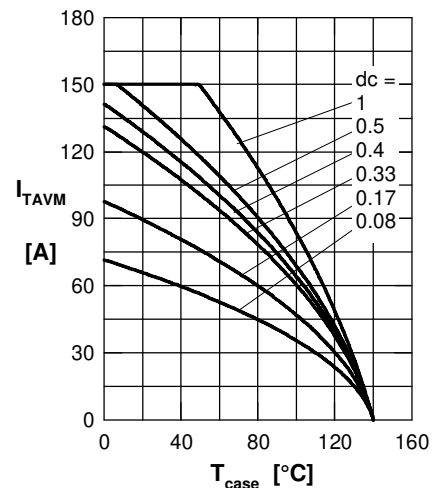

 Fig. 5 Gate controlled delay time t_{gd}


Fig. 6 Max. forward current at case temperature

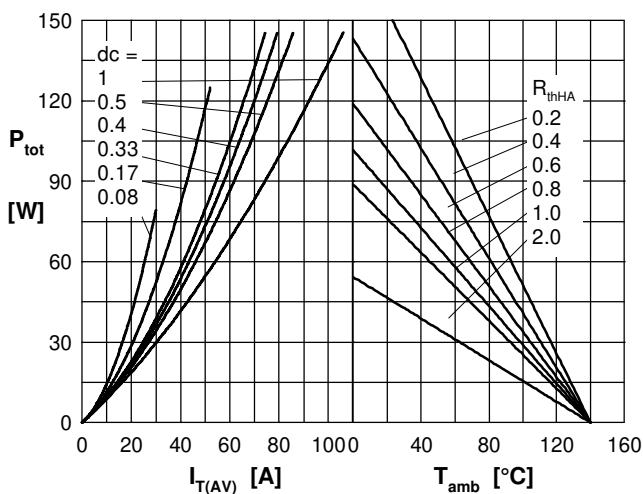
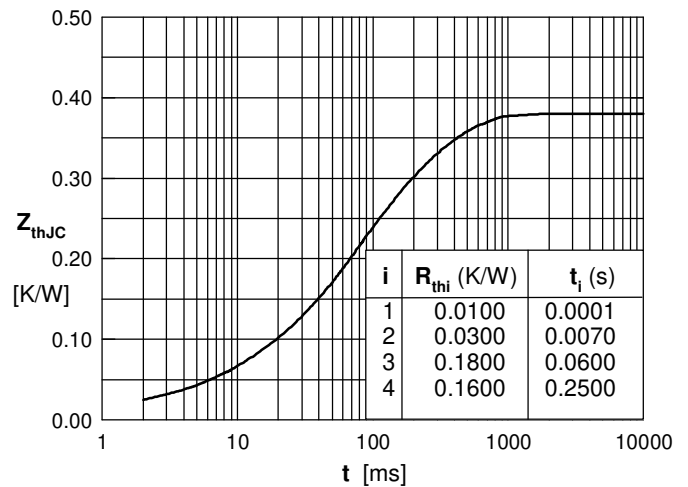

 Fig. 7a Power dissipation versus direct output current
 Fig. 7b and ambient temperature


Fig. 8 Transient thermal impedance junction to case